

Gamma irradiation of ATLAS18 ITk strip sensors affected by static charge

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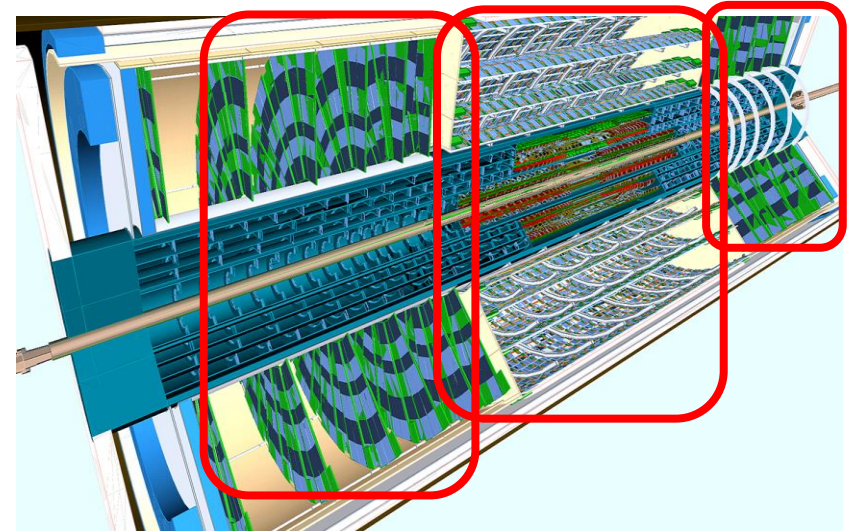
The ITk Detector for the HL-LHC

- For the HL-LHC, the ATLAS tracking system will be replaced with all-silicon detector: the **Inner Tracker (ITk)**

- ITk Pixel detector
- ITk Strip detector

- 4 concentric cylindrical layers in barrel
- 6+6 disks in endcaps
- 17,888 sensors
- 165 m² of silicon
- 60 million strips
- Dose: up to 53.2 Mrad
- Fluence: up to $1.1 \times 10^{15} \text{ 1MeV } n_{\text{eq}} \text{ cm}^{-2}$

- ITk detector designed to withstand harsh HL-LHC environment
 - 4,000 fb⁻¹ over 10 years, $L_{\text{peak}} = 7.5 \times 10^{34} \text{ cm}^{-2} \text{ s}^{-1}$, $\mu \sim 200$

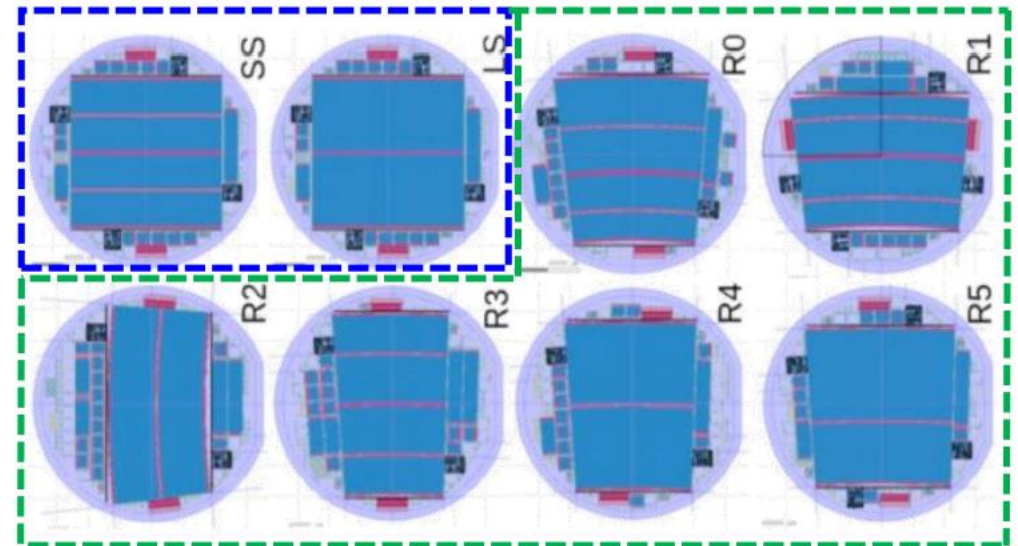
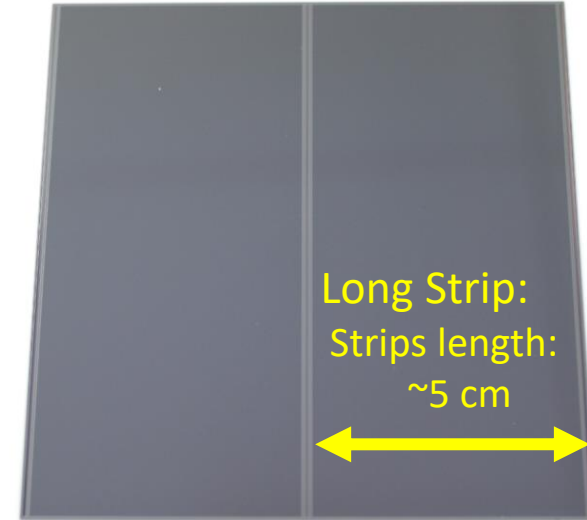
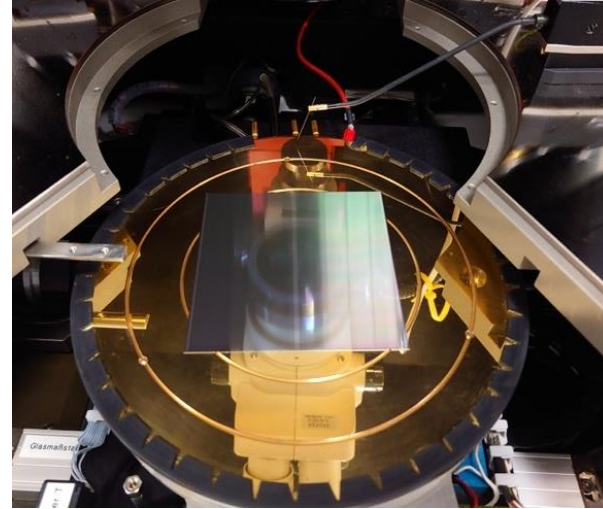


More about

- ITk Pixel in Jo's [talk](#)
- ITk Strip in Igor's [talk](#)
- ITk Strip Endcap in Laura's [poster](#)

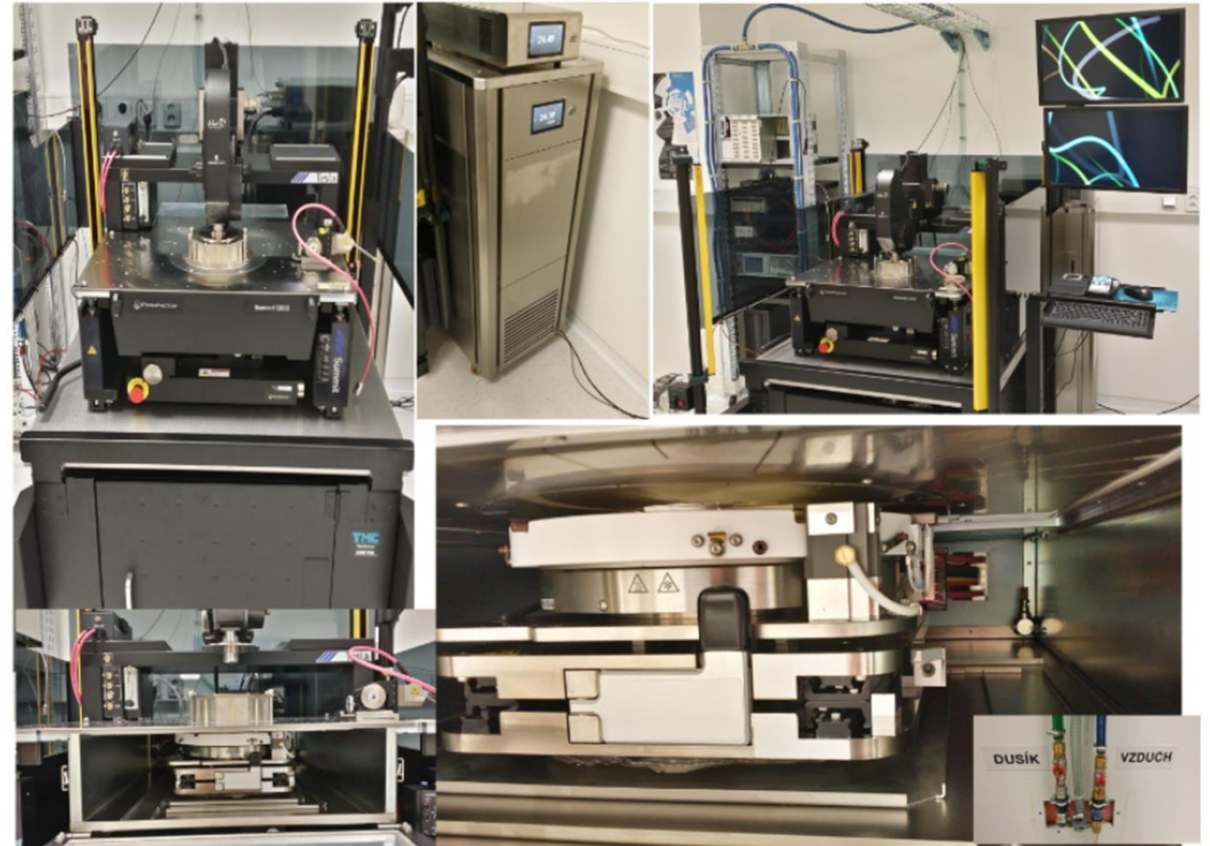
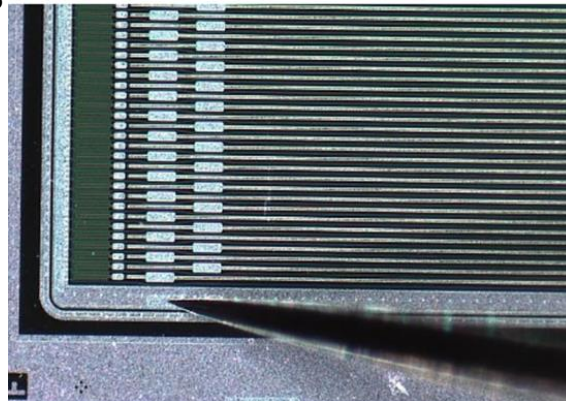
Si Strip Sensors by HPK

- n^+ -on-p, 320 μm thick, single sided microstrips
- AC-coupled strips with polysilicon biasing
- **Barrel sensors** – square geometry
 - Strip pitch 75.5 μm
 - Short strips (SS) 24.1 mm long
 - Long strips (LS): 48.3 mm long
- **Endcap sensors:** trapezoidal
 - 6 sensor geometries
 - Pitch 70-80 μm
 - Strip length: 15-60 mm depending on radius
- Sensor production of total amount of 20800 sensors started in HPK in 2021 and is scheduled for completion in 2025



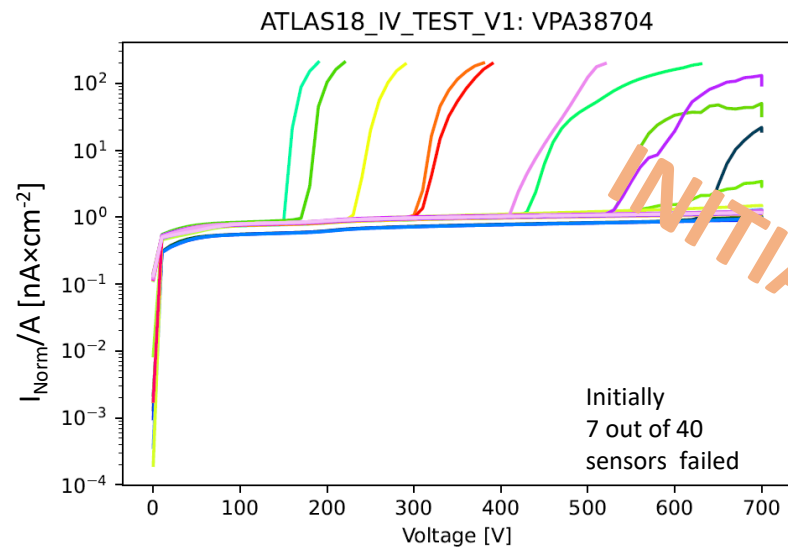
QC main sensor testing

- upon delivery ATLAS performs detailed measurements of sensors to monitor quality of all fabricated devices and to ensure that their characteristics are within specifications defined by ATLAS collaboration
- **QC tests**
 - Mechanical tests (bow and thickness)
 - Current-voltage (IV)
 - Capacitance-voltage (CV)
 - Leakage Current Stability: 5%-10% sampling
 - Full Strip Tests (I_{PIN} , C_{COUPL} , R_{BIAS}/R_{INT}): 2%-10% sampling
- **QC sensor testing sites**
 - KEK/Tsukuba
 - SCIPP
 - U of Cambridge
 - QMUL
 - FZU Prague
 - SFU/TRIUMF
 - Carleton U

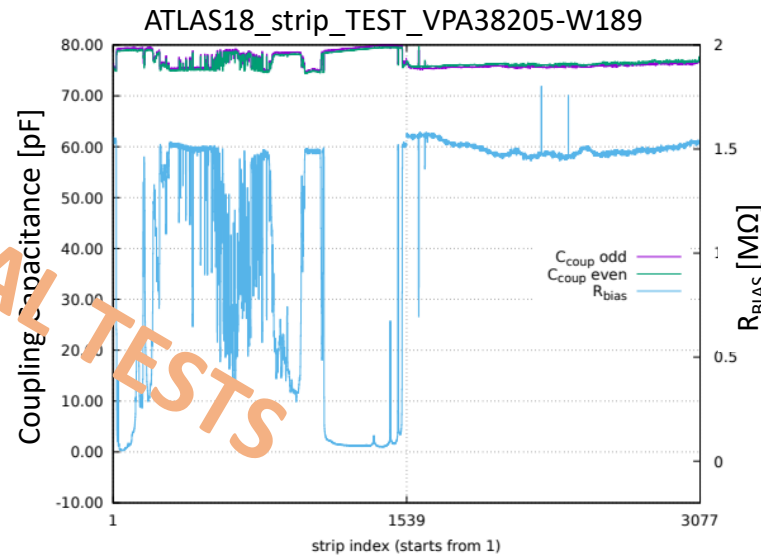


Specific Issues observed in QC testing

- Most sensors show high quality in QC tests
- In several production batches, a number of sensors failed the electrical QC tests:
 1. Early breakdown in IV: Breakdown Voltage (V_{BD}) < 500 V (specs: > 500V)
 2. Areas with low interstrip isolation in full strip tests
 3. Current instabilities during long-term current stability testing and failures in IV after the stability tests



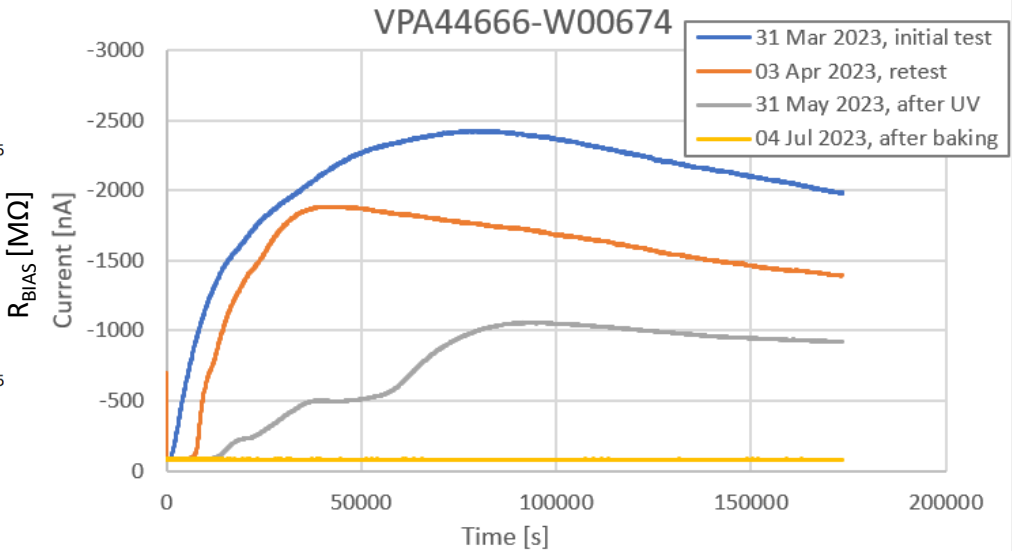
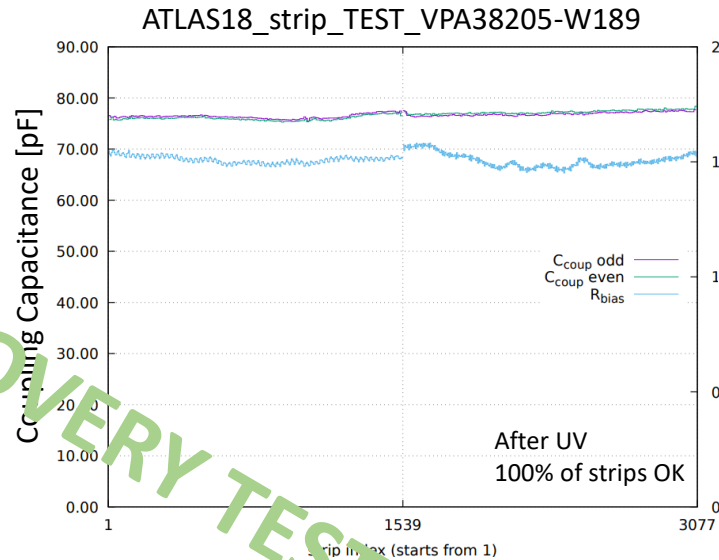
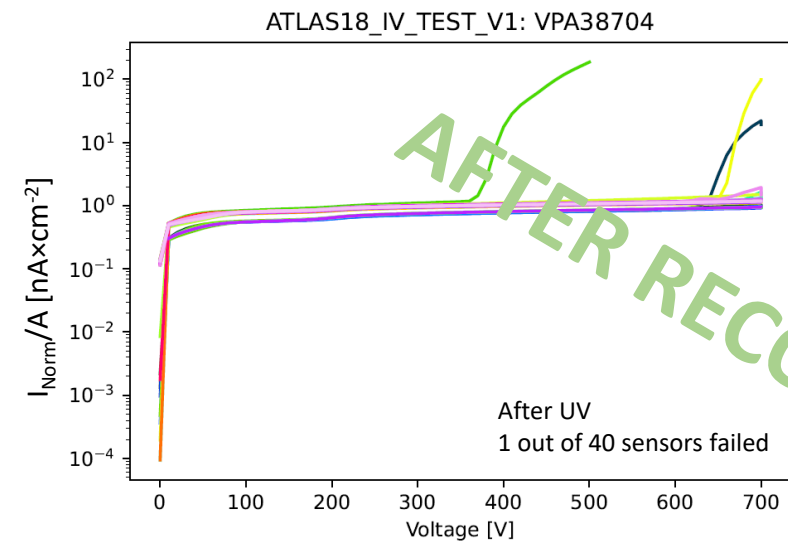
219	228	234	240	248	255	262
220	229	235	241	250	256	263
221	230	236	242	251	257	264
222	231	237	244	252	258	266
226	232	238	245	253	259	267
227	233	239	247	254		



static charge measurement

- Strong correlation between observed electrical failures and high electrostatic charge (up to ~ 100's V/inch)
- Electrostatic charge accumulated on the surface of the sensor
 - in the strip area can lead to the loss of interstrip isolation
 - close to the edge and bias ring can cause instability of current or low breakdown voltage

- Introduced sensor recovery techniques:
 1. irradiation of the sensor surface with **UV-A** and **UV-C** light
 2. application of the intensive flow of ionized gas
 3. subject the sensors to high-temperature exposure
 4. dry storage over days / weeks



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227	233	239	247	254		

[ATL-COM-ITK-2023-060.pdf](#)

Sensors affected by static charge in real experiment

- Despite implementation of recovery techniques, it is still possible that some affected sensors won't be identified by the sensor QC testing or that the electrostatic events could occur later during tracker assembly.
- **Hypothesis:**
 - Will the sensor issues caused by static charge be “cured” by ionization in the real experiment? If so, how quickly?
- **Study:**
 - Irradiation of affected sensors by ^{60}Co gamma rays with aim to determine whether it can effectively resolve early breakdown (BD) or low interstrip isolation, and if so, to determine the TID and real experiment duration required for such a cure
- **Plan:**
 - Select 3 sensors with early BD and 3 sensors with low interstrip isolation for the irradiation study
 - Irradiate just 2 (with early BD) + 2 (with low interstrip isolation) sensors to a few consecutive target TIDs
 - 1+1 sensors keep as REFERENCE samples - no irradiation, but transport, storage, and handling identical to irradiated sensors

Samples selected for the study

- 3 sensors with early break-down

	Initial IV test BDV [V]	IV test just before irradiation. (2 month in dry storage) BDV [V]
R1-W607	150 V	160 V
R1-W617	150 V	150 V
R1-W650	150 V	200 V

Reference sample

- 3 sensors with low interstrip isolation areas

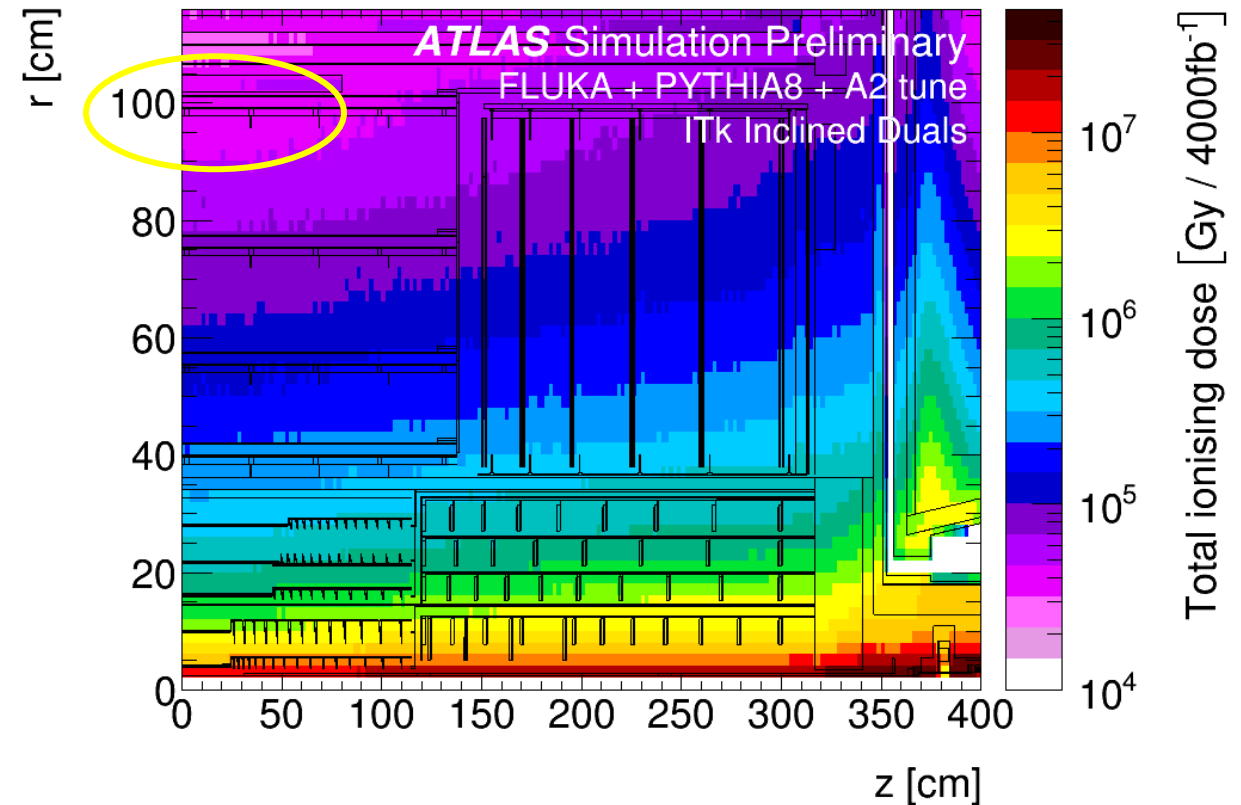
	Initial Full Strip test # of bad strips	Full strip test just before irradiation. (2 month in dry storage) # of bad strips
R1-W635	40	40
R1-W620	26	18
R3-W1014	28	24

Reference sample

Estimation of few consecutive target TIDs

- The worst case for curing affected sensors by electrostatic charge are regions where TID is minimal (it will take longer to get sensors cured):
 - Central region of the outermost barrel cylinder, with 5.9 Mrad target dose (including 1.5 safety factor)
 - Targets TIDs planned for this experiment:

Real experiment duration	TID [krad]
1 week	11
1 month	49
6 months	195
1 year	590
2 years	1200
...	

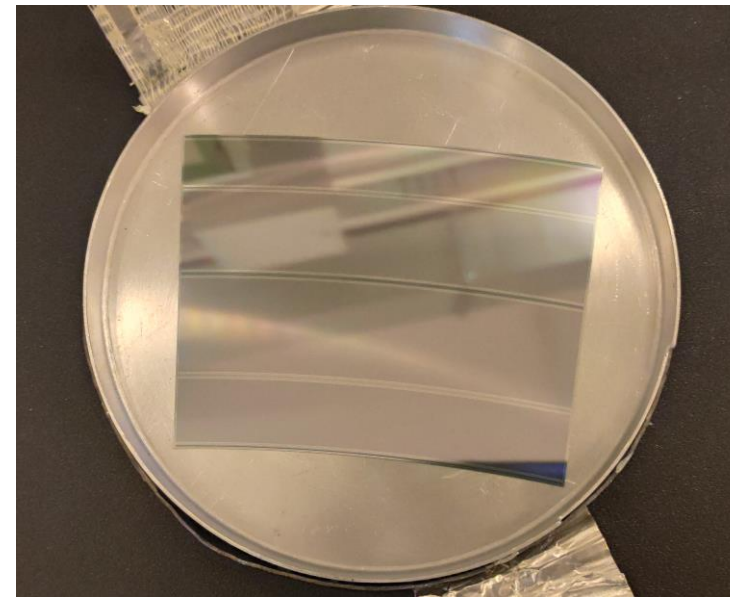


https://twiki.cern.ch/twiki/bin/view/AtlasPublic/RadiationSimulationPublicResults#Phase_II_Upgrade_Mar_2018_AN1

Gamma irradiation

- UJP Praha a.s.: gamma from Co60,
- Sensors irradiated individually in Charge Particle Equilibrium (CPE) box => sensor surface free
- Distance from source: ~28 cm
- Reference samples were physically moved inside the CPE box, taken out, but not subjected to irradiation.

Irrad. campaign	TID [krad]	Dose Rate [krad/min]	Irradiation time [s]
1.	11	1.024	644
2.	1.5	1.026	88
3.	1.5	1.026	88



Results after irradiation of 11krad

	IV just before irradiation: BDV [V]	IV after irradiation: BDV [V]
R1-W607	160 V	>600 V*
R1-W617	150 V	>680 V*
R1-W650	200 V	250 V

* The LabVIEW program was interrupted because the current limit of 20uA was reached

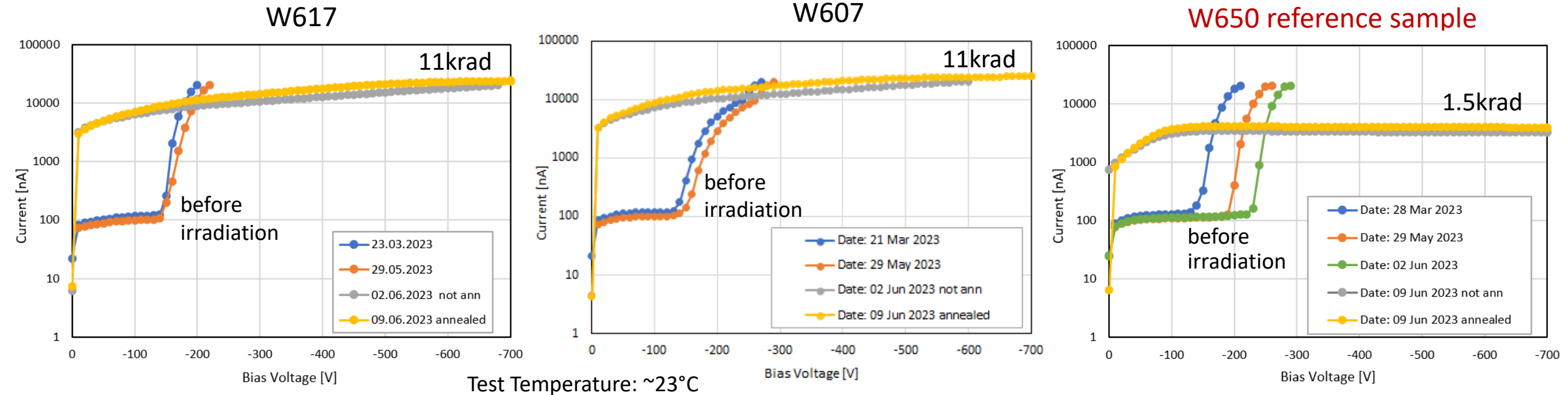
Reference sample

	Full strip test before irradiation: # of bad strips	Full strip test after irradiation: # of bad strips
R1-W635	40	0
R1-W620	18	18
R3-W1014	24	0

Reference sample

- Gamma irradiated sensors **cured**: BDV increased and low interstrip isolation areas disappeared
- Reference sensor (transported and handled alongside the other sensors, not subjected to irradiation) **not recovered**.
- Gamma irradiation resolved issues successfully during initial planned step of irradiation with 11 krad (~1 week in the real experiment) => further irradiations to higher TIDs were not needed
- Instead, the reference samples were irradiated to an even lower TID of 1.5 krad (~1 day in the real experiment).

IV before and after gamma irradiation



- Early BD of sensors W617 and W607 disappeared after gamma irradiation to 11krad.
- Early BD of reference sample W650 was not resolved (green line). W650 was transported and handled alongside W617 and W607 but not subjected to irradiation.
- After later gamma irradiation of the reference sample W650 to 1.5 krad the early BD disappeared too.
- Leakage current is $\sim 100\times$ higher after 11krad gamma irradiation, $\sim 35\times$ higher after 1.5krad.
- Annealing at 60°C for 80 minutes does not decrease the current.

R3-W1014: Full Strip Tests

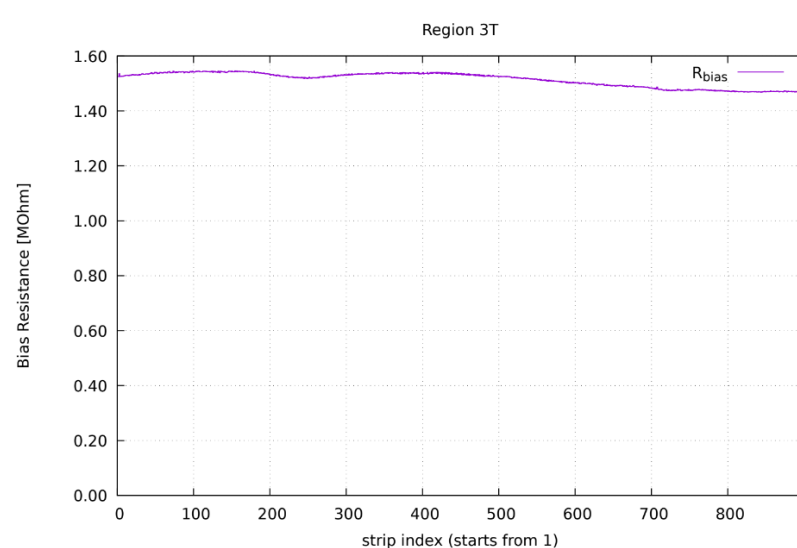
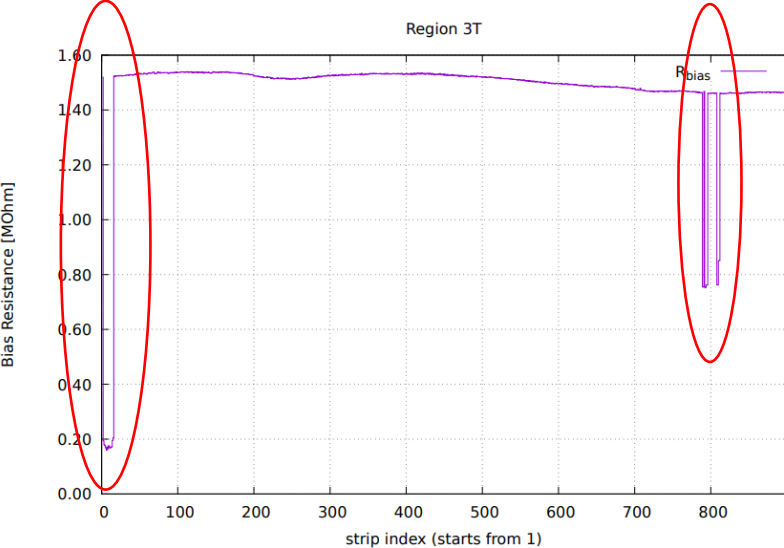
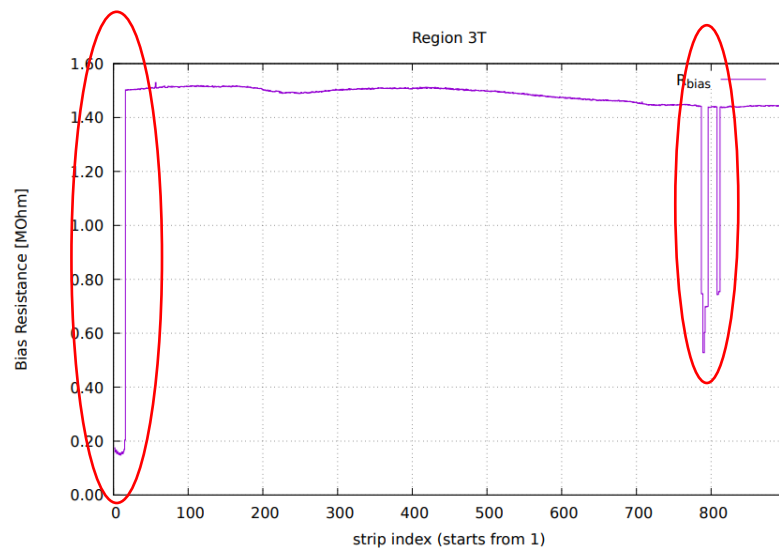
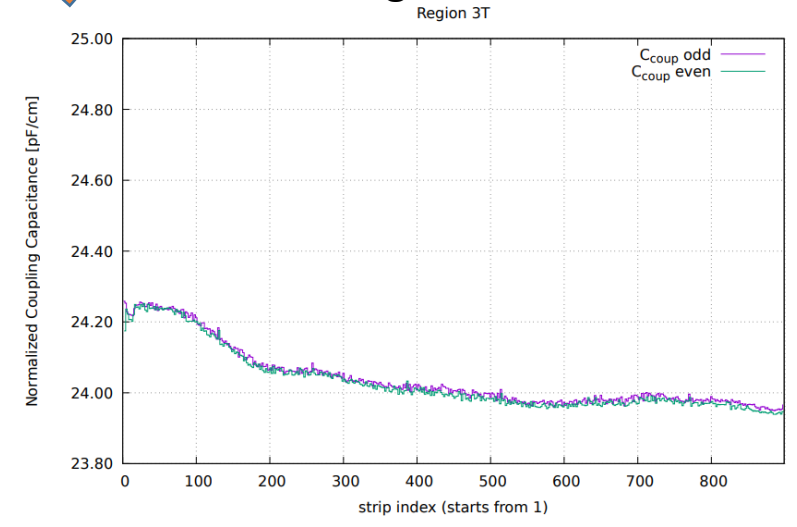
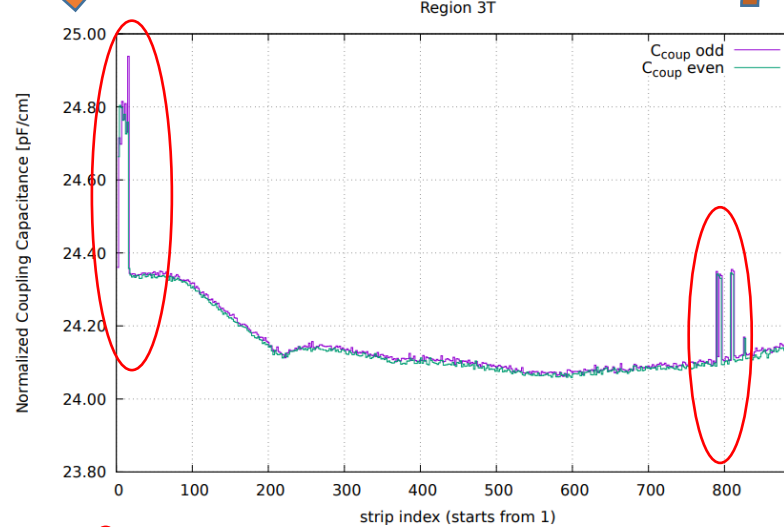
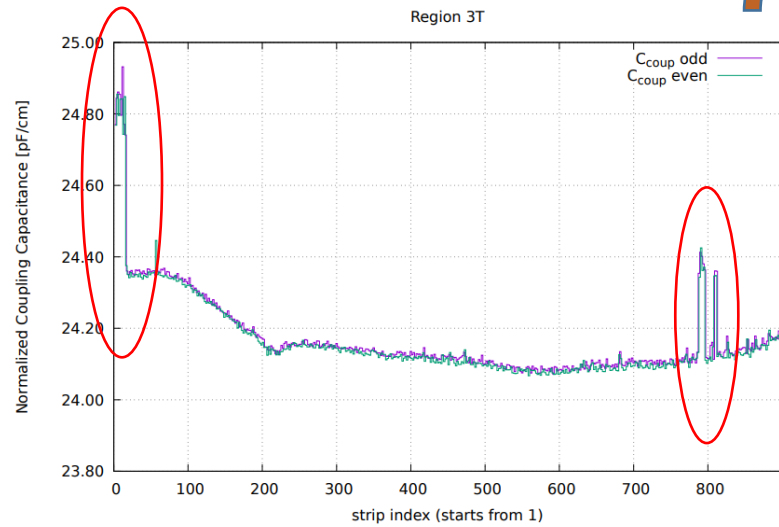
Dry storage

Irradiation

Initial test before irrad.

Test right before irrad.

Test after gamma 11krad



R1-W0635: Full Strip Tests

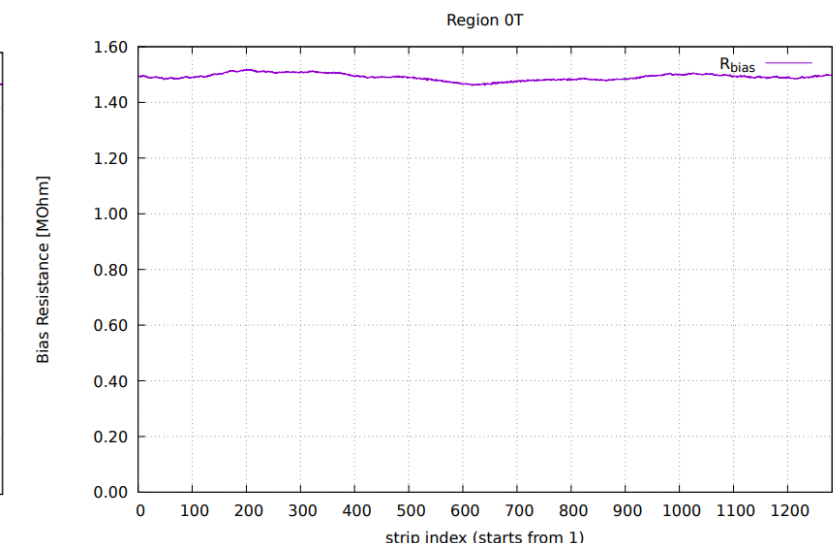
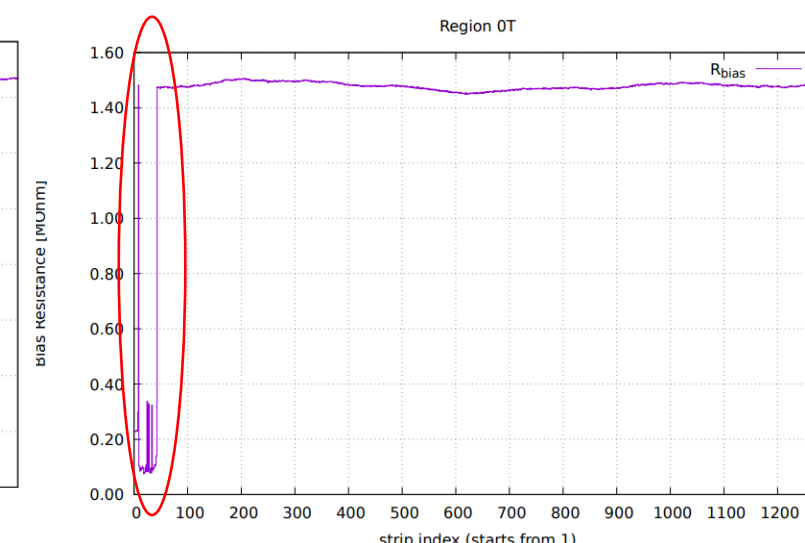
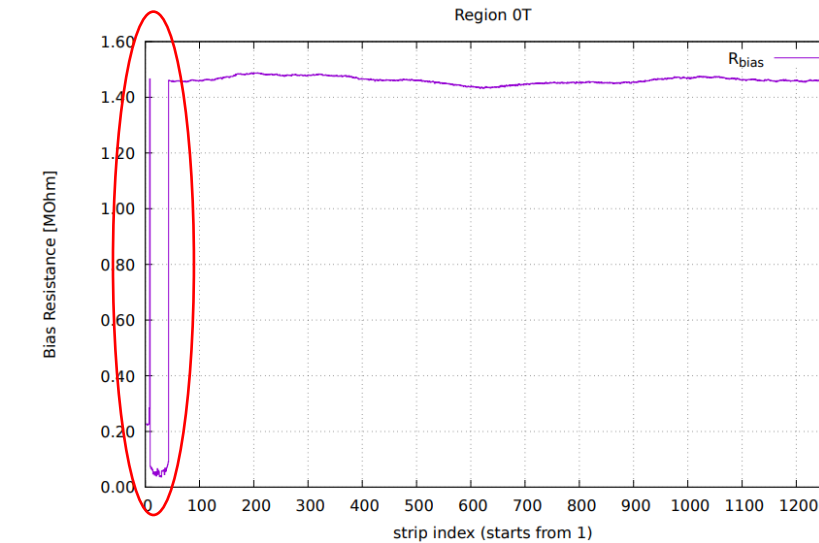
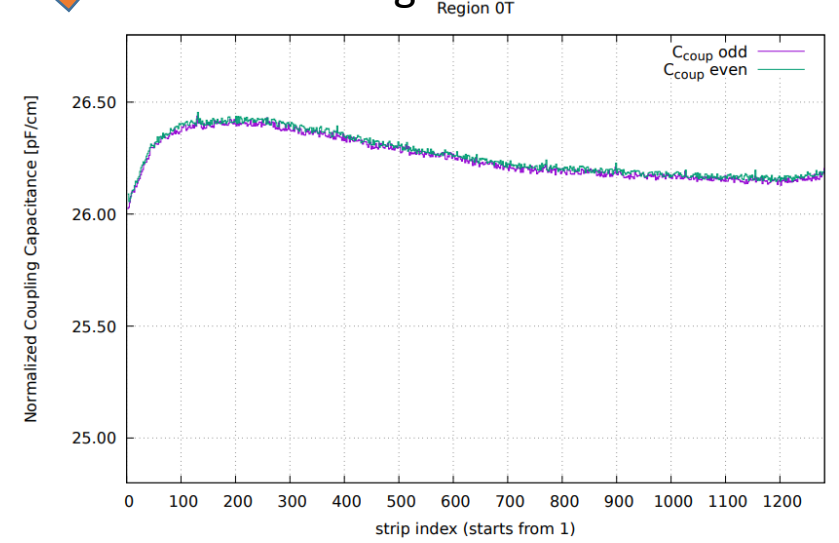
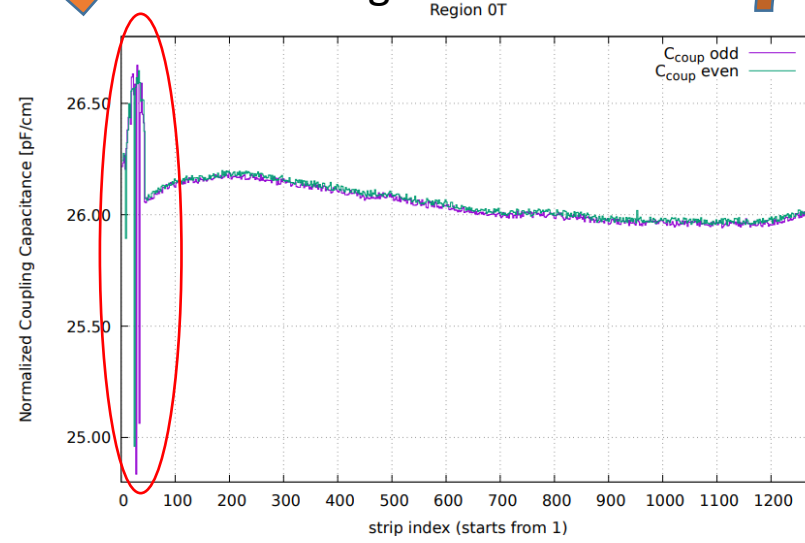
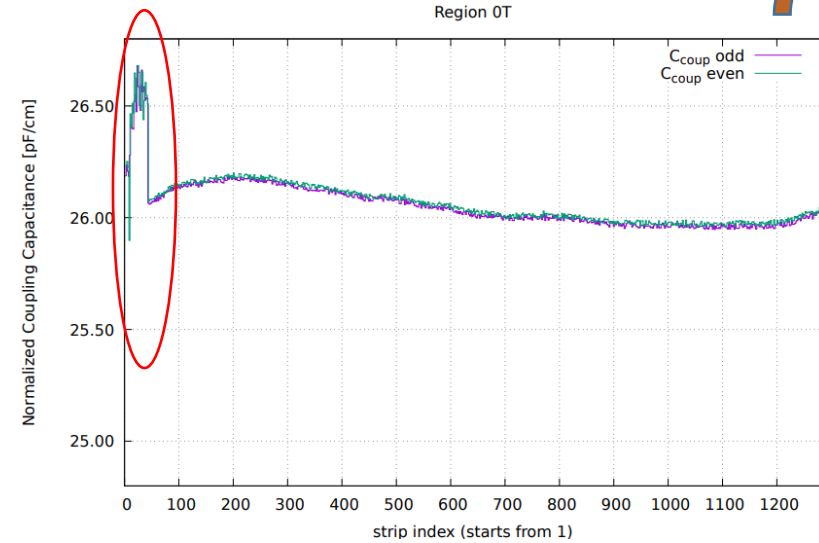
Dry storage

Irradiation

Initial test before irrad.

Test right before irrad.

Test after gamma 11krad



R1-W620: Full Strip Tests - reference sample

Dry storage

Irradiation

Initial test before irrad.

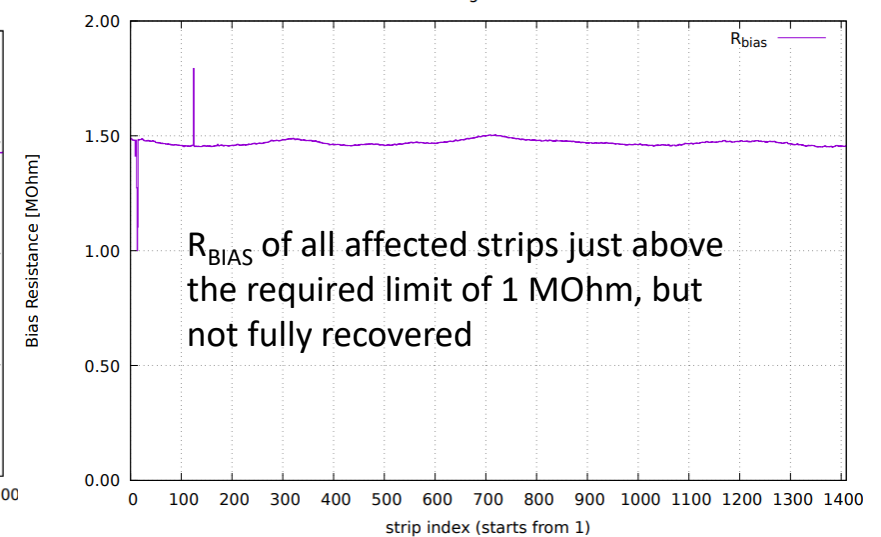
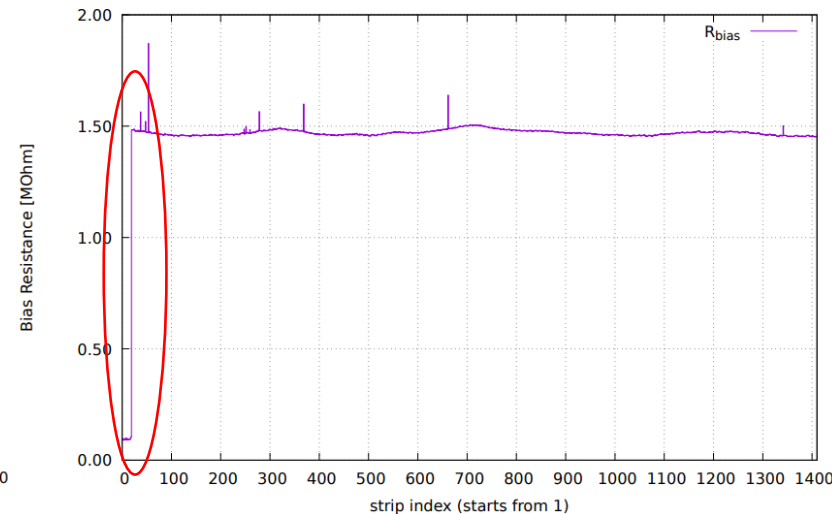
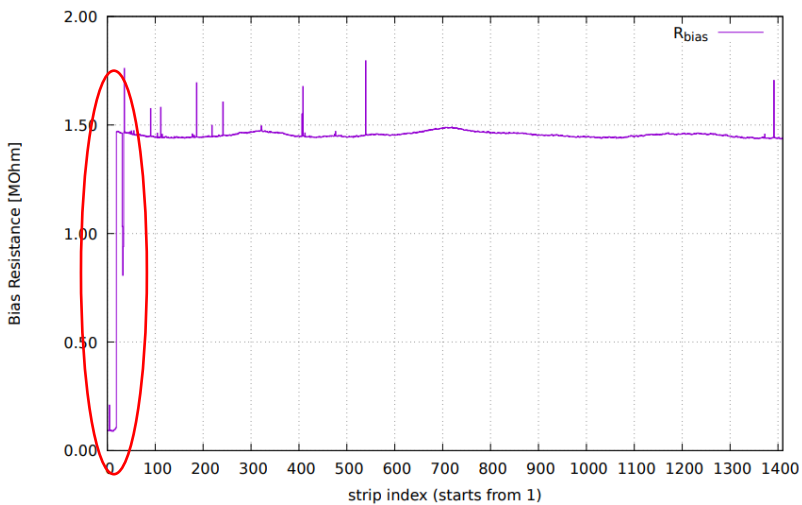
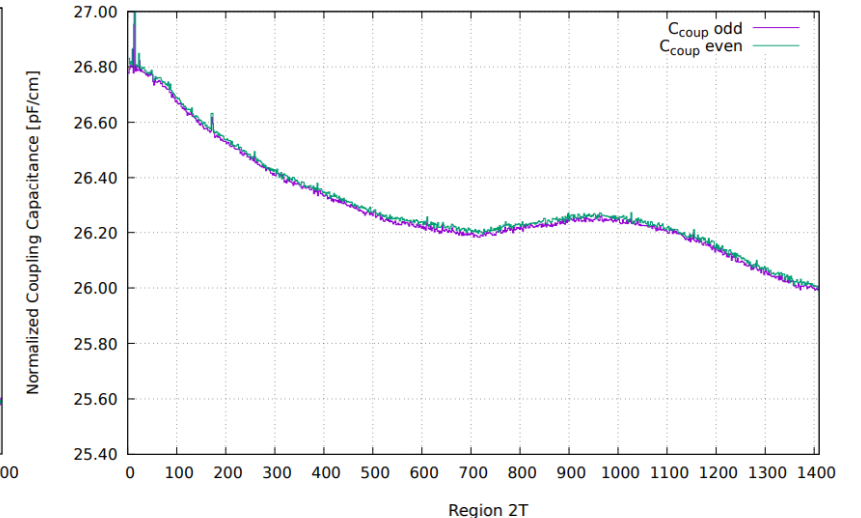
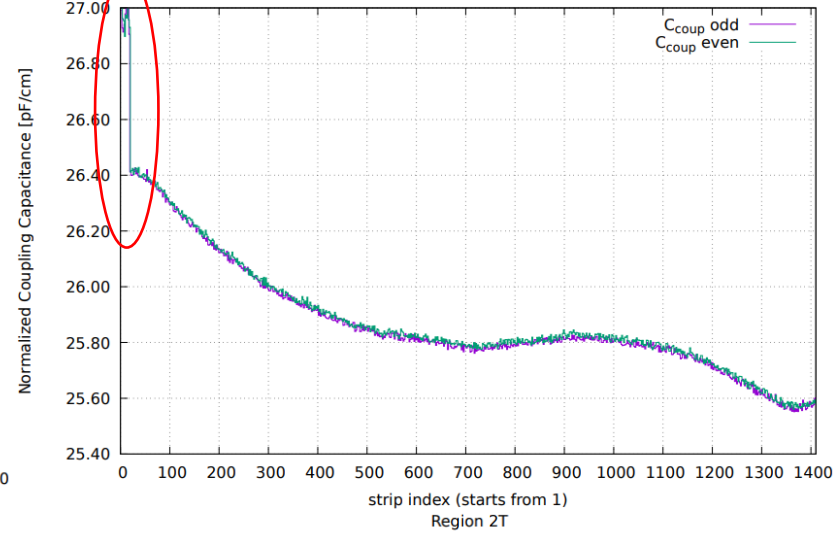
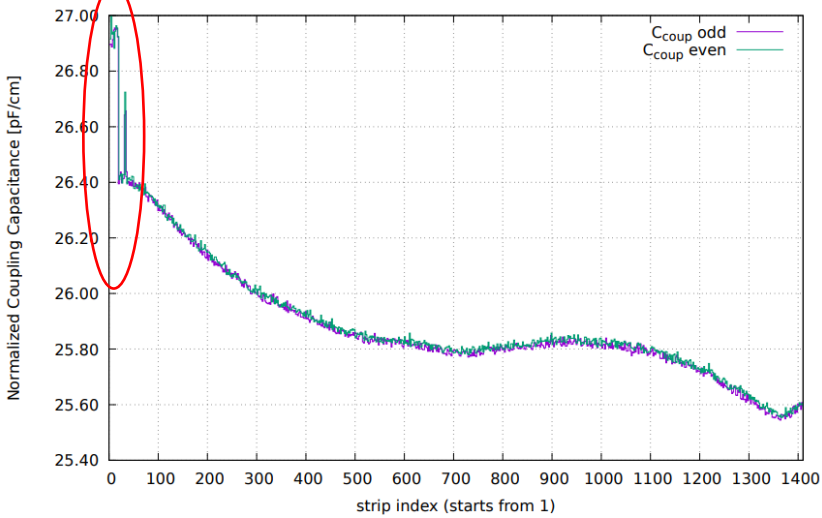
Test after "not irradiation"

Test after gamma 1.5krad

Region 2T

Region 2T

Region 2T



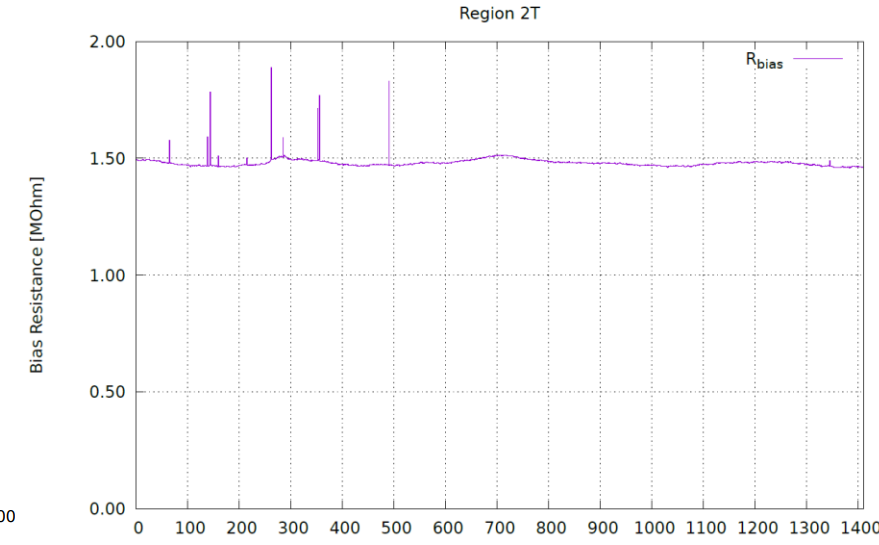
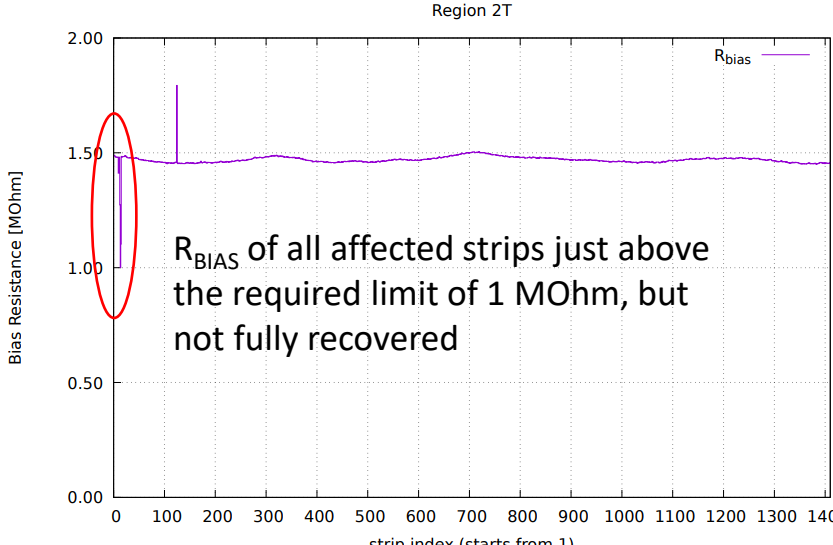
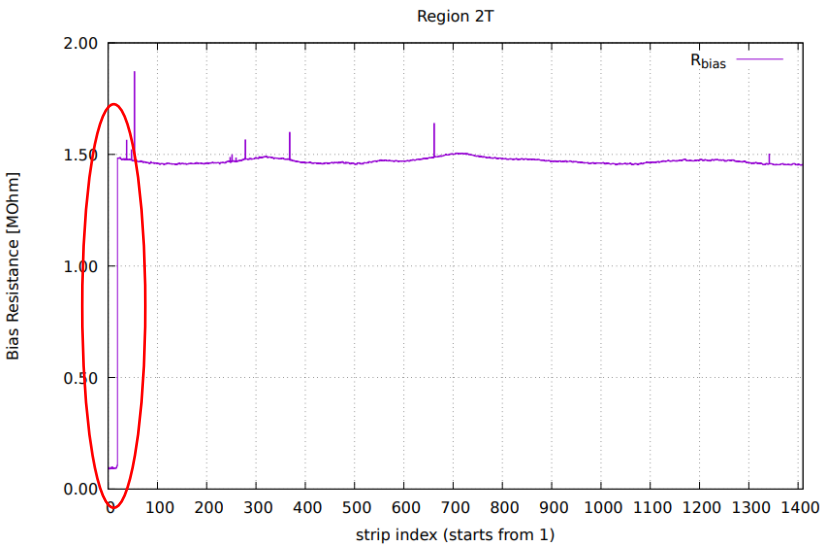
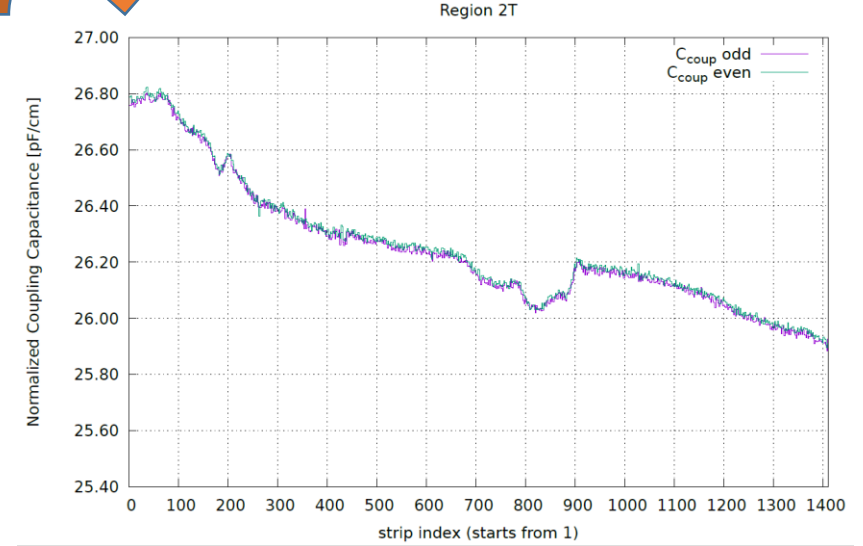
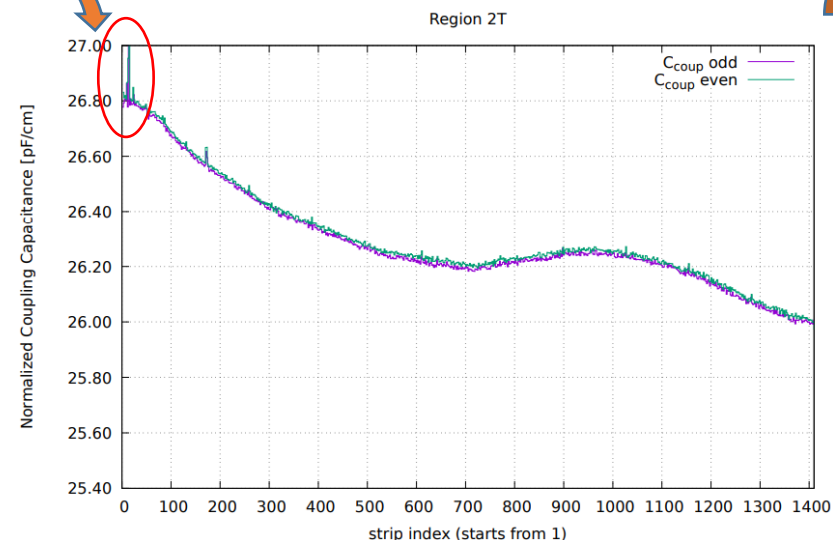
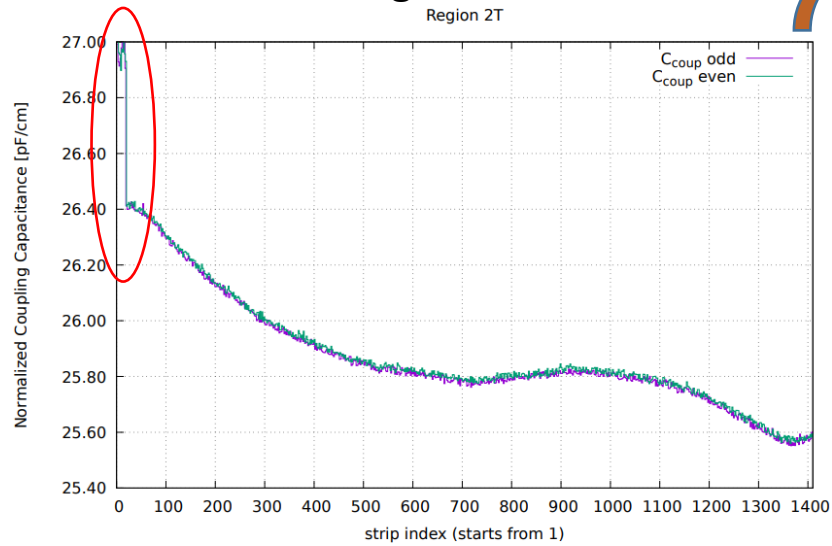
Test right before irradiad.

Irradiation

Test after gamma 1.5krad

2nd Irradiation

Test after additional 1.5 krad



Summary

- TID of 11 krad (\approx 1 week in real experiment) successfully resolved early breakdown and low interstrip isolation issues of sensors, related to high electrostatic charge accumulated on the surface of these sensors.
- Even a small TID like 1.5 krad (\approx 1 day in real experiment) resolved the low breakdown voltage and significantly improved also strip test results. R_{BIAS} and C_{COUP} values of all strips were within the specifications.
- Additional TID of 1.5 krad cured the low interstrip isolation issue completely.
- **It implies that the electrostatic sensor issues will be resolved completely within two days of a real experiment operation.**